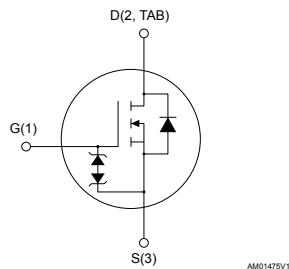
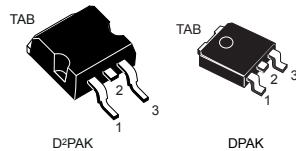


# N-channel 650 V, 1.2 $\Omega$ typ., 4 A MDmesh™ M2 Power MOSFETs in D<sup>2</sup>PAK and DPAK packages



AM01479V1

## Features

Order code	$V_{DS}$	$R_{DS(on)max.}$	$I_D$	Package
STB6N65M2	650 V	1.35 $\Omega$	4 A	D <sup>2</sup> PAK
STD6N65M2				DPAK

- Extremely low gate charge
- Excellent output capacitance ( $C_{OSS}$ ) profile
- 100% avalanche tested
- Zener-protected

## Applications

- Switching applications

## Description

These devices are N-channel Power MOSFETs developed using the MDmesh™ M2 technology. Thanks to their strip layout and improved vertical structure, these devices exhibit low on-resistance and optimized switching characteristics, rendering them suitable for the most demanding high-efficiency converters.



### Product status

STB6N65M2

STD6N65M2

### Product summary

Order code	STB6N65M2
Marking	6N65M2
Package	D <sup>2</sup> PAK
Packing	Tape and reel
Order code	STD6N65M2
Marking	6N65M2
Package	DPAK
Packing	Tape and reel

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	4	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	2.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	16	A
$P_{TOT}$	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	60	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	50	V/ns
$T_j$	Operating junction temperature range	-55 to 150	$^\circ\text{C}$
$T_{stg}$	Storage temperature range		

1. Pulse width limited by  $T_{jmax}$ .
2.  $I_{SD} \leq 4\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ;  $V_{DS\ peak} < V_{(BR)DSS}$ ,  $V_{DD} = 400\text{ V}$ .
3.  $V_{DS} \leq 520\text{ V}$ .

**Table 2. Thermal data**

Symbol	Parameter	Value		Unit
		D <sup>2</sup> PAK	DPAK	
$R_{thj-case}$	Thermal resistance junction-case	2.08		$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	30	50	$^\circ\text{C}/\text{W}$

1. When mounted on 1 inch<sup>2</sup> FR-4, 2 Oz copper board.

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j\ max$ )	0.5	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	100	mJ

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}, V_{GS} = 0\text{ V}$	650			V
$I_{DSS}$	Zero gate voltage drain current	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}, T_C = 125\text{ °C}^{(1)}$			100	$\mu\text{A}$
$I_{GSS}$	Gate body leakage current	$V_{DS} = 0\text{ V}, V_{GS} = \pm 25\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 2\text{ A}$		1.2	1.35	$\Omega$

1. Defined by design, not subject to production test.

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz}, V_{GS} = 0\text{ V}$	-	226	-	$\mu\text{F}$
$C_{oss}$	Output capacitance			12.8		
$C_{rSS}$	Reverse transfer capacitance			0.65		
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0\text{ V},$ $V_{DS} = 0\text{ to }520\text{ V}$	-	114	-	$\mu\text{F}$
$R_g$	Gate input resistance	$f = 1\text{ MHz}, I_D = 0\text{ A}$	-	6.5	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 520\text{ V}, I_D = 4\text{ A},$ $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 13. Test circuit for gate charge behavior)	-	9.8	-	nC
$Q_{gs}$	Gate-source charge			1.7		
$Q_{gd}$	Gate-drain charge			4		

1.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

**Table 6. Switching times**

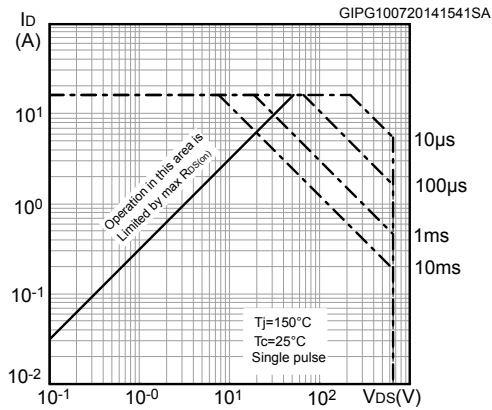
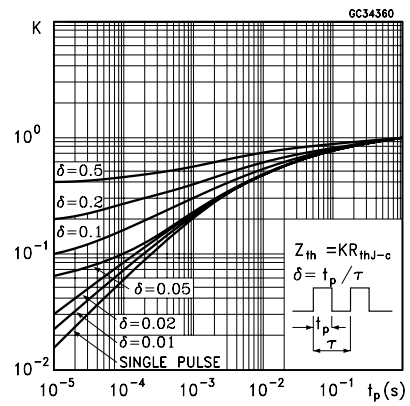
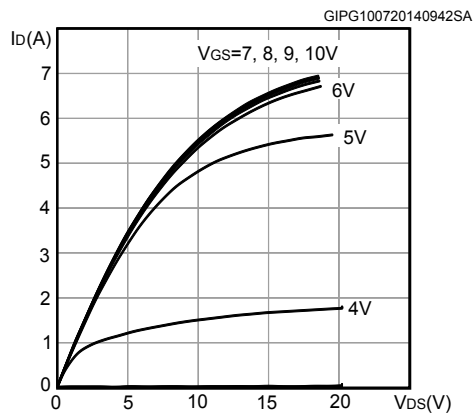
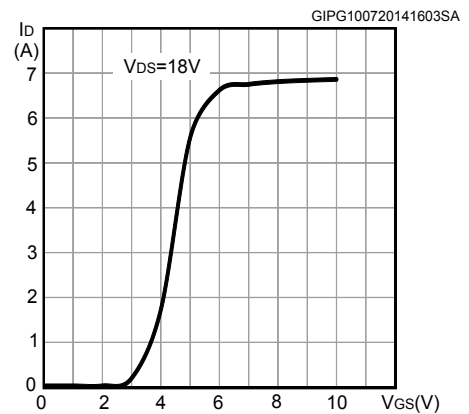
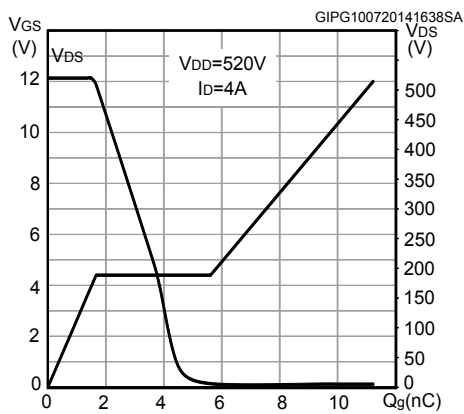
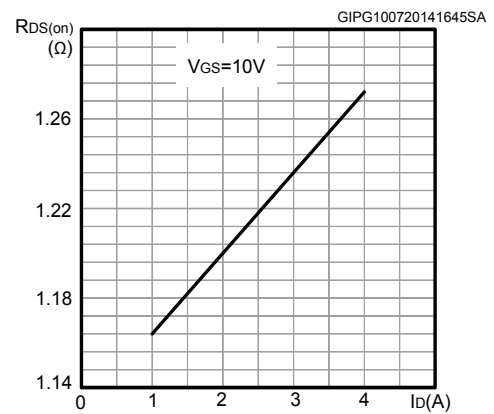
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}, I_D = 2\text{ A},$ $R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$ (see Figure 12. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	19	-	ns
$t_r$	Rise time			7		
$t_{d(off)}$	Turn-off delay time			6.5		
$t_f$	Fall time			20		

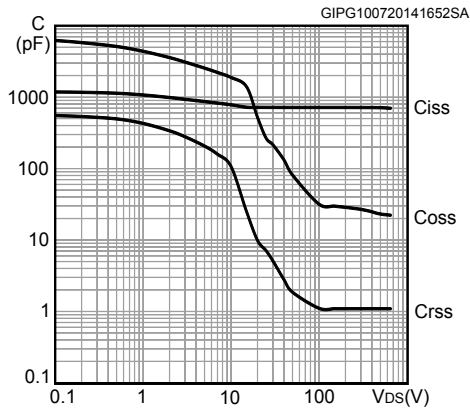
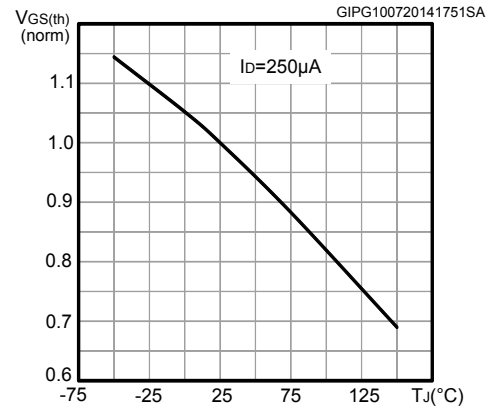
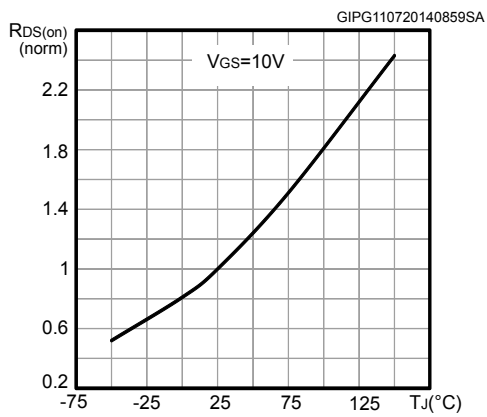
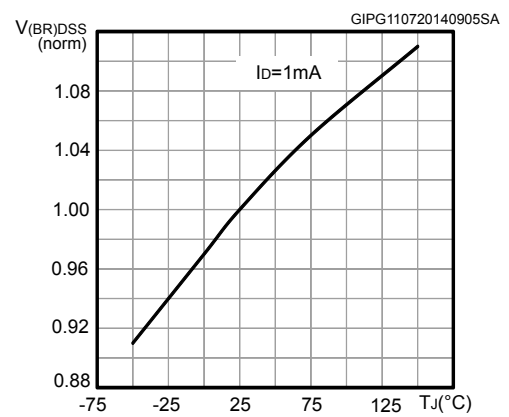
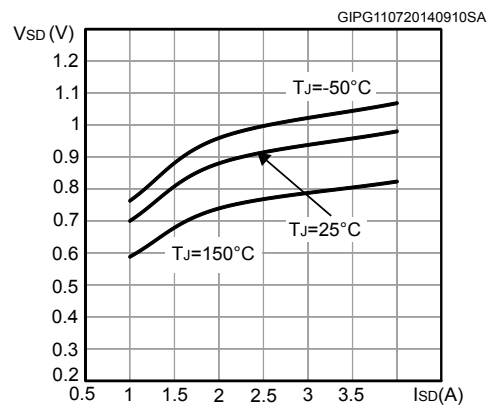
**Table 7. Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		4	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				16	
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 4\text{ A}$ , $V_{GS} = 0\text{ V}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 4\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		260		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60\text{ V}$ (see Figure 14. Test circuit for inductive load switching and diode recovery times)	-	1.2		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current			9.2		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 4\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		400		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$	-	1.84		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	(see Figure 14. Test circuit for inductive load switching and diode recovery times)		9.1		A

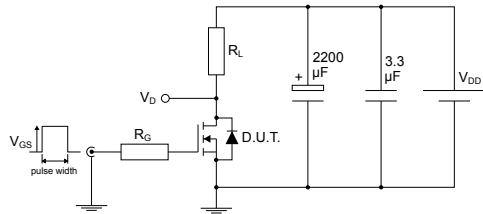
1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

## 2.1 Electrical characteristics (curves)

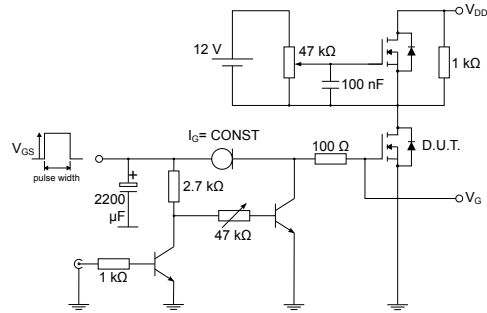
**Figure 1. Safe operating area**

**Figure 2. Thermal impedance**

**Figure 3. Output characteristics**

**Figure 4. Transfer characteristics**

**Figure 5. Gate charge vs gate-source voltage**

**Figure 6. Static drain-source on-resistance**


**Figure 7. Capacitance variations**

**Figure 8. Normalized gate threshold voltage vs temperature**

**Figure 9. Normalized on-resistance vs temperature**

**Figure 10. Normalized V(BR)DSS vs temperature**

**Figure 11. Source-drain diode forward characteristics**


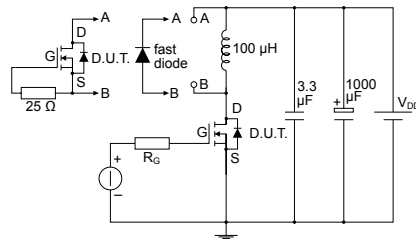
### 3 Test circuits

**Figure 12. Test circuit for resistive load switching times**


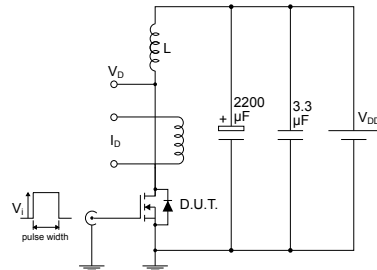
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**Figure 13. Test circuit for gate charge behavior**


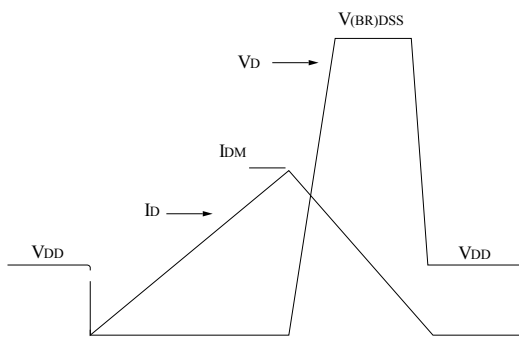
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**Figure 14. Test circuit for inductive load switching and diode recovery times**


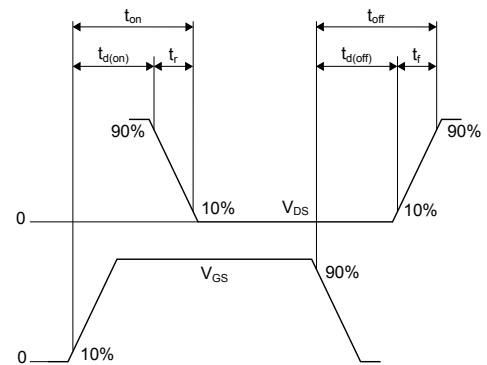
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**Figure 15. Unclamped inductive load test circuit**


AM01471v1

**Figure 16. Unclamped inductive waveform**


AM01472v1

**Figure 17. Switching time waveform**


AM01473v1

## 4 Package information

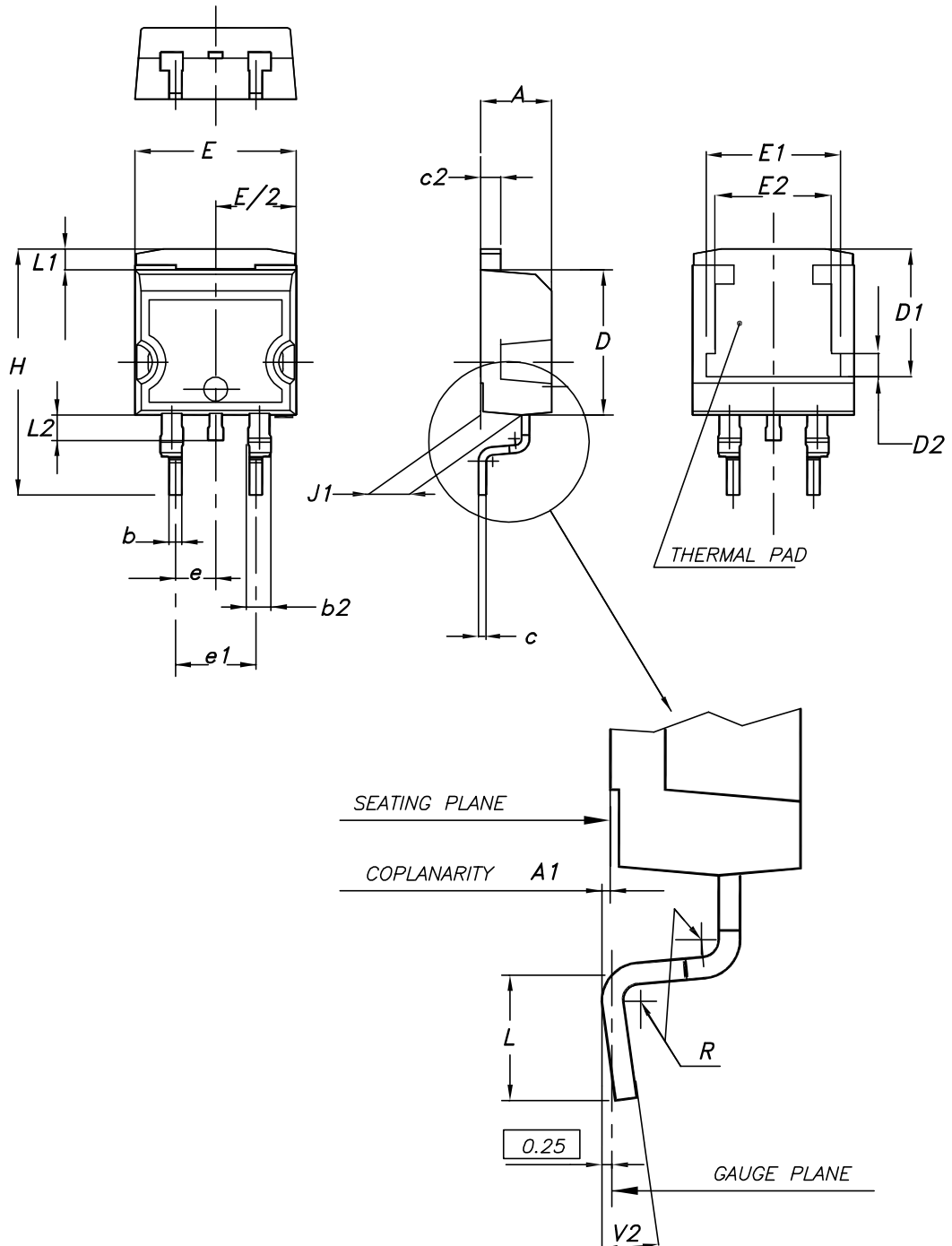
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In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK®** packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.



#### 4.1 D<sup>2</sup>PAK (TO-263) type A package information

Figure 18. D<sup>2</sup>PAK (TO-263) type A package outline



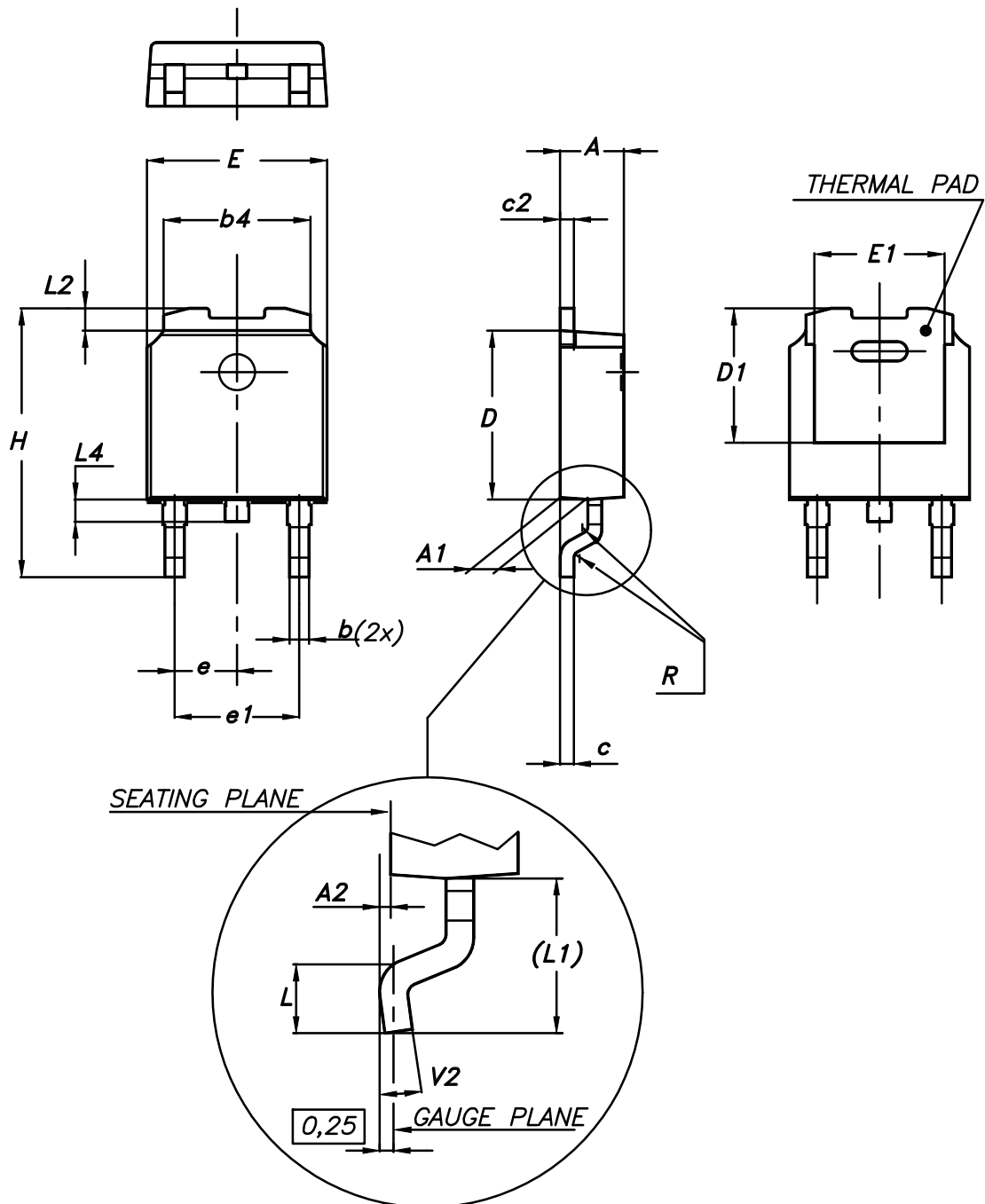
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**Table 8. D<sup>2</sup>PAK (TO-263) type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.30	8.50	8.70
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

## 4.2 DPAK (TO-252) type A package information

Figure 19. DPAK (TO-252) type A package outline



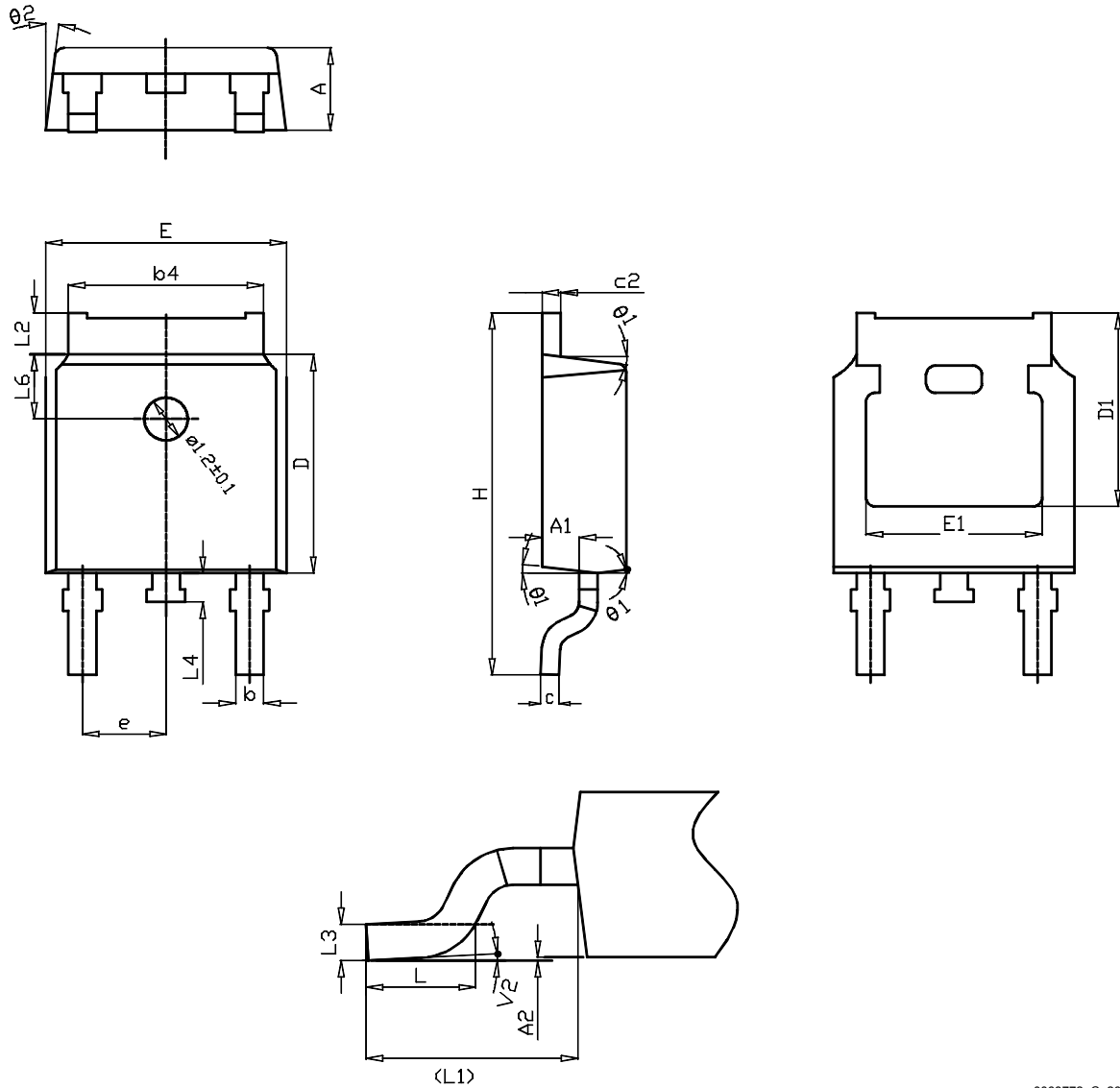
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**Table 9. DPAK (TO-252) type A mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

### 4.3 DPAK (TO-252) type C package information

Figure 20. DPAK (TO-252) type C package outline



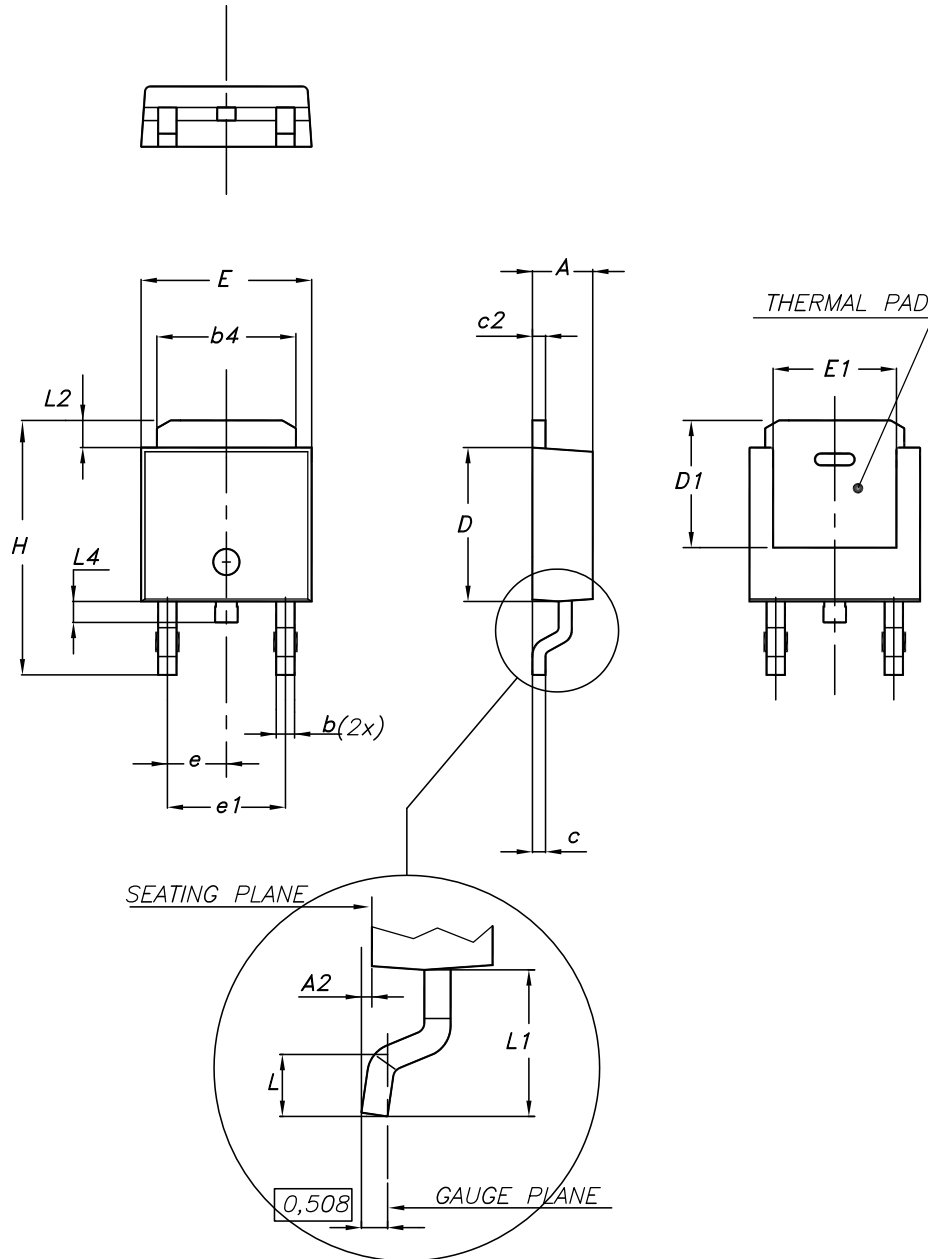
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**Table 10. DPAK (TO-252) type C mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.25		
E	6.50	6.60	6.70
E1	4.70		
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.90		1.25
L3	0.51 BSC		
L4	0.60	0.80	1.00
L6	1.80 BSC		
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

#### 4.4 DPAK (TO-252) type E package information

Figure 21. DPAK (TO-252) type E package outline

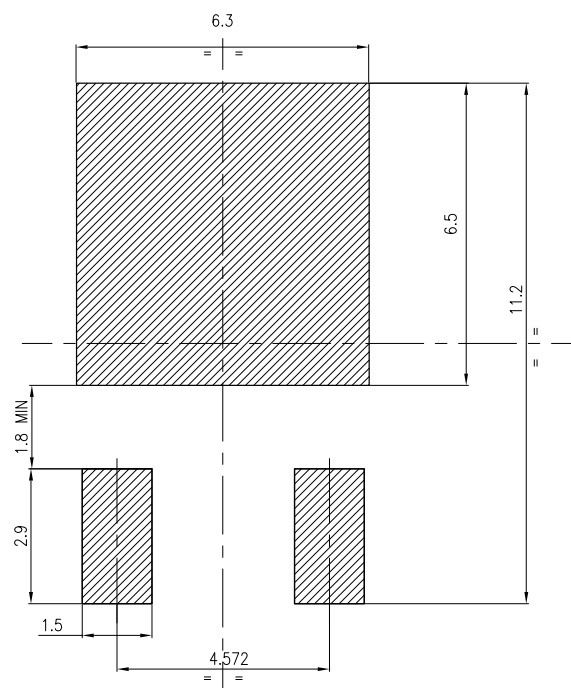


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**Table 11. DPAK (TO-252) type E mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.18		2.39
A2			0.13
b	0.65		0.884
b4	4.95		5.46
c	0.46		0.61
c2	0.46		0.60
D	5.97		6.22
D1	5.21		
E	6.35		6.73
E1	4.32		
e		2.286	
e1		4.572	
H	9.94		10.34
L	1.50		1.78
L1		2.74	
L2	0.89		1.27
L4			1.02

**Figure 22. DPAK (TO-252) recommended footprint (dimensions are in mm)**

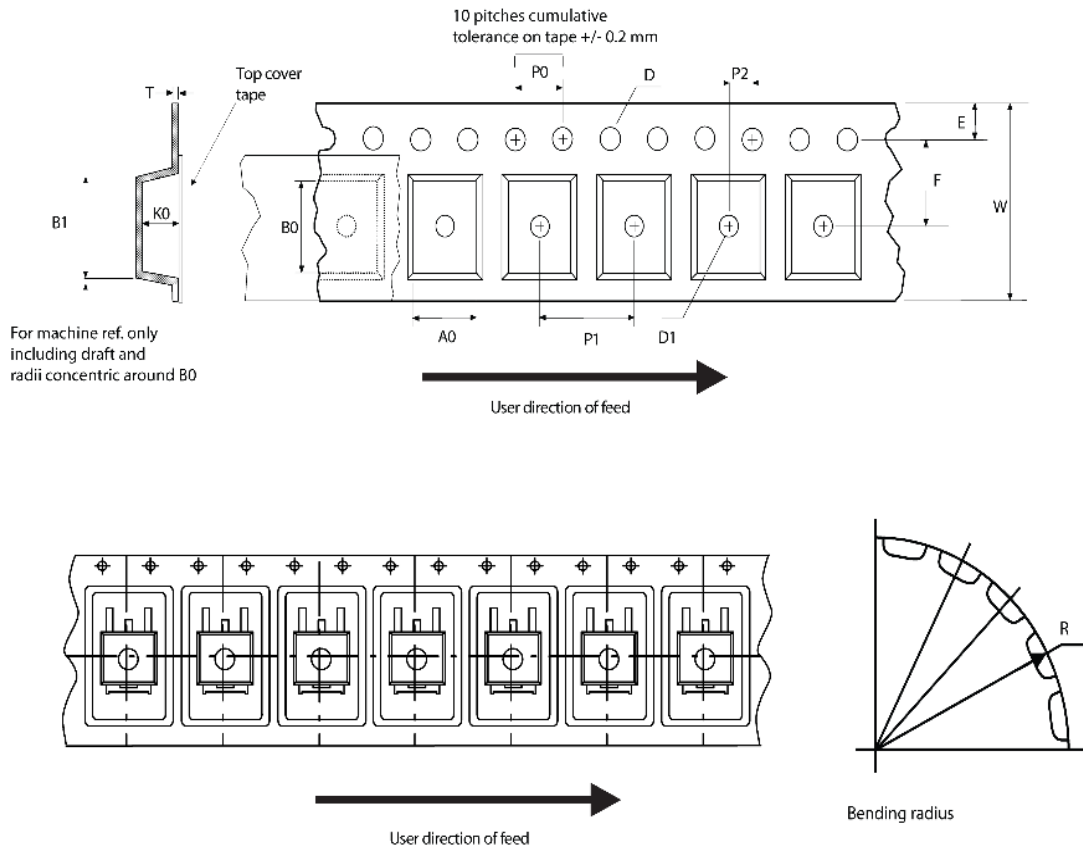


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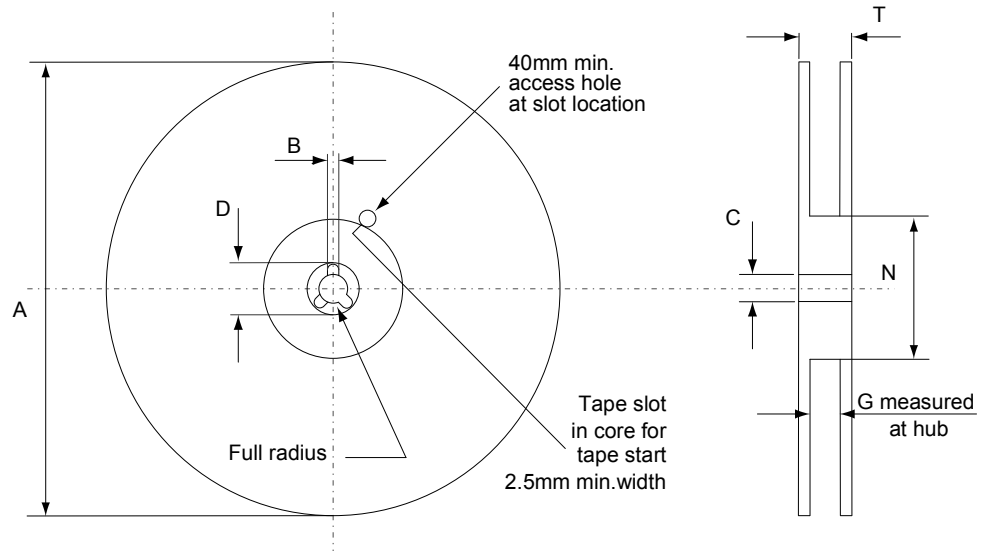


## 4.5 D<sup>2</sup>PAK and DPAK packing information

Figure 23. Tape outline



AM08852v1

**Figure 24. Reel outline**


AM06038v1

**Table 12. D<sup>2</sup>PAK tape and reel mechanical data**

Tape			Reel			
Dim.	mm		Dim.	mm		
	Min.	Max.		Min.	Max.	
A0	10.5	10.7	A		330	
B0	15.7	15.9	B	1.5		
D	1.5	1.6	C	12.8	13.2	
D1	1.59	1.61	D	20.2		
E	1.65	1.85	G	24.4	26.4	
F	11.4	11.6	N	100		
K0	4.8	5.0	T		30.4	
P0	3.9	4.1	Base quantity Bulk quantity			
P1	11.9	12.1				1000
P2	1.9	2.1				1000
R	50					
T	0.25	0.35				
W	23.7	24.3				

**Table 13. DPAK tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

## Revision history

**Table 14. Document revision history**

Date	Version	Changes
04-Aug-2014	1	First release.
05-Dec-2018	2	Removed maturity status indication from cover page. The document status is production data. Updated <a href="#">Section 4 Package information</a> . Minor text changes.

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